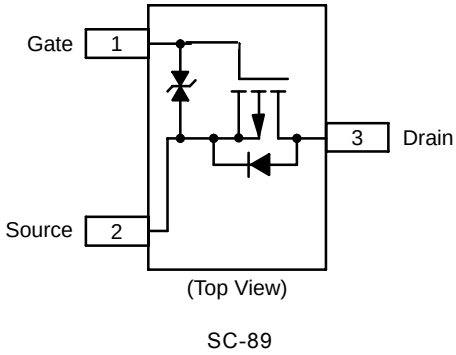
SI1013CX

P-Channel 1.8-V (G-S) MOSFET



SC-89

FEATURES

- TrenchFET® Power MOSFET: 1.8-V Rated
- Gate-Source ESD Protected: 2000 V
- High-Side Switching
- Low On-Resistance: 1.2 Ω
- Low Threshold: 0.8 V (typ)
- Fast Switching Speed: 14 ns
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

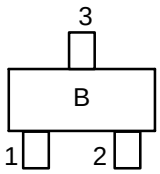
BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

MARKING DIAGRAM



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±6		
Continuous Drain Current (T_J = 150°C)[b]	T_A = 25°C	I_D	-400	-350	mA
	T_A = 85°C		-300	-275	
Pulsed Drain Current[a]		I_{DM}	-1000		
Continuous Source Current (diode conduction)[b]		I_S	-275	-250	
Maximum Power Dissipation[b] for SC-75	T_A = 25°C	P_D	175	150	mW
	T_A = 85°C		90	80	
Maximum Power Dissipation[b] for SC-89	T_A = 25°C		275	250	
	T_A = 85°C		160	140	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

Notes
d. Pulse width limited by maximum junction temperature.
e. Surface Mounted on FR4 Board.

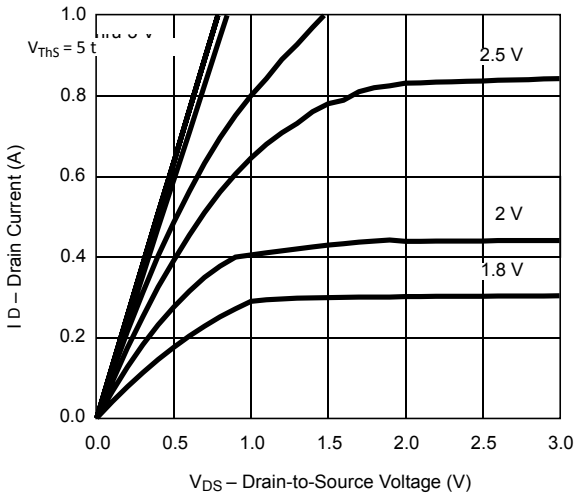
SPECIFICATIOHS [T_A = 25°C UHhESS OTHERWISE HOTED)						
Parameter	**Symbol**	**Test Condition**	**Min**	**Typ**	**Max**	**Unit**
Static						
Thate Threshold Voltage	$V_{ThS(th)}$	V_{DS} = V_{ThS}, I_D = –250 µA	–0.45			V
Thate-Body Leakage	I_{ThSS}	V_{DS} = 0 V, V_{ThS} = T4.5 V		T1	T2	µA
Zero Thate Voltage Drain Current	I_{DSS}	V_{DS} = –16 V, V_{ThS} = 0 V		–0.3	–100	nA
		V_{DS} = –16 V, V_{ThS} = 0 V, T_J = 85°C			–5	µA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = –5 V, V_{ThS} = –4.5 V	–700			mA
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{ThS} = –4.5 V, I_D = –350 mA		0.8	1.2	fi
		V_{ThS} = –2.5 V, I_D = –300 m A		1.2	1.6	
		V_{ThS} = –1.8 V, I_D = –10 m A		1.8	2.7	
Forward Transconductance[a]	g_{fs}	V_{DS} = –10 V, I_D = –250 mA		0.4		S
Diode Forward Voltage[a]	V_{SD}	I_S = –150 mA, V_{ThS} = 0 V		–0.8	–1.2	V
Dynamic[b]						
Total Thate Charge	Q_g	V_{DS} = –10 V, V_{ThS} = –4.5 V, I_D = –250 mA		1500		pC
Thate-Source Charge	Q_{gs}			150		
Thate-Drain Charge	Q_{gd}			450		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = –10 V, R_L = 47 fi I_D ÷ –200 mA, V_{ThEN} = –4.5 V, R_{Th} = 10 fi		5		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(off)}$			35		
Fall Time	t_f			11		

Notes
a. Pulse test; pulse width S 300 µs, duty cycle S 2%.
b. Thuaranteed by design, not subject to production testing.

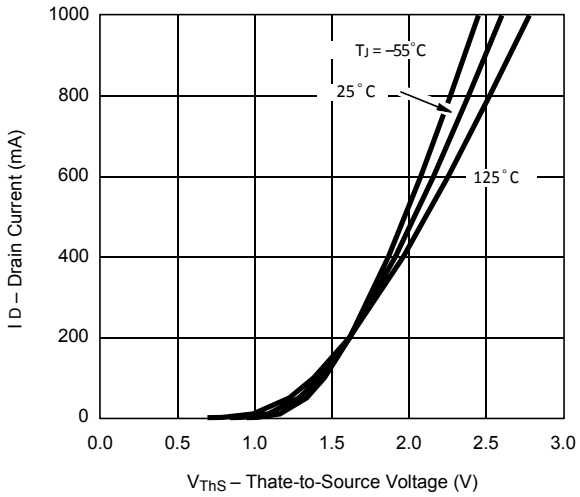
TYPICAh CHARACTERISTICS [T_A = 25 °C UHhESS HOTED)

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.

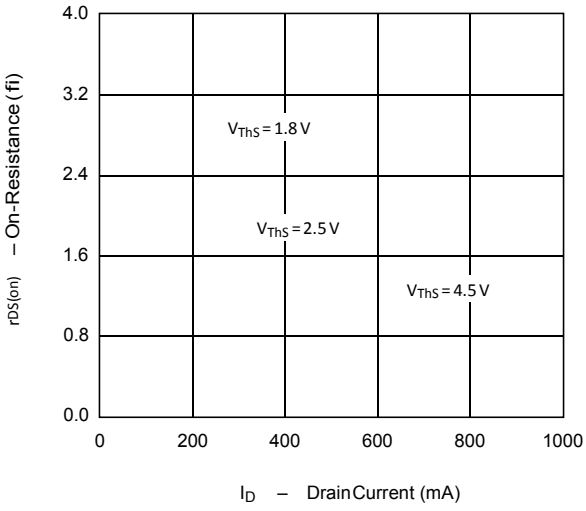
Output Characteristics



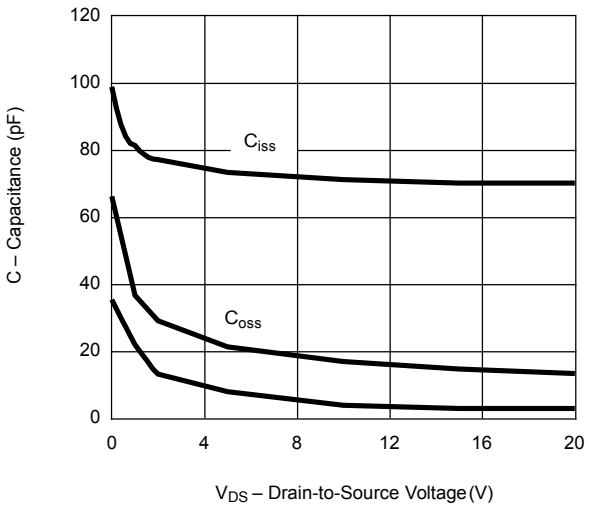
Transfer Characteristics



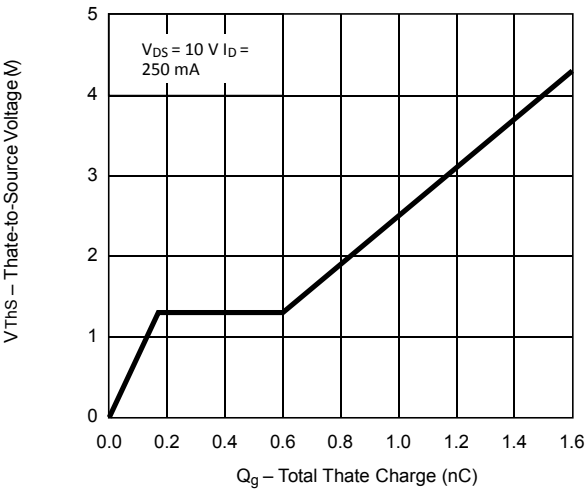
On-Resistance vs. Drain Current



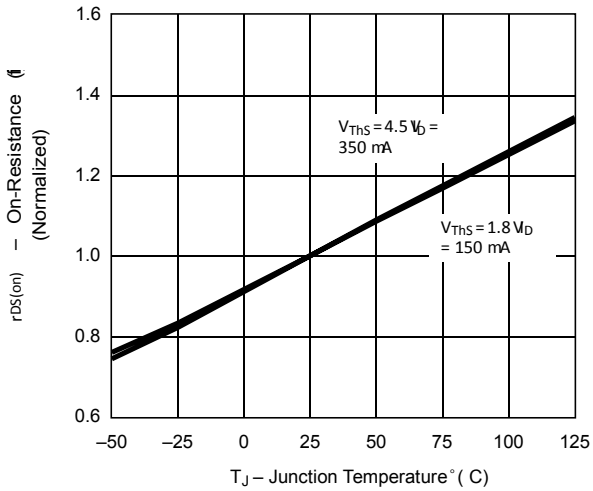
Capacitance



Gate Charge

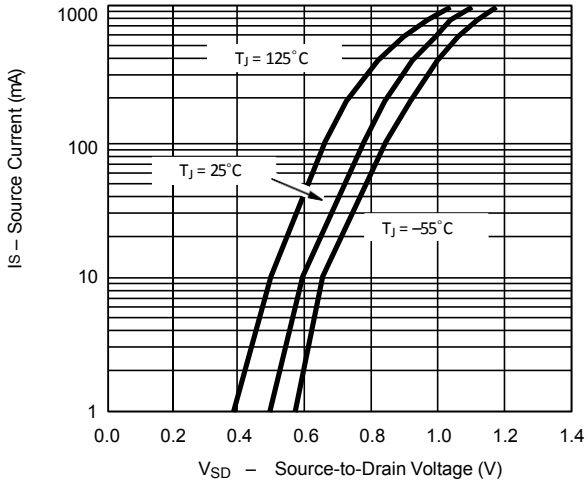


On-Resistance vs. Junction Temperature

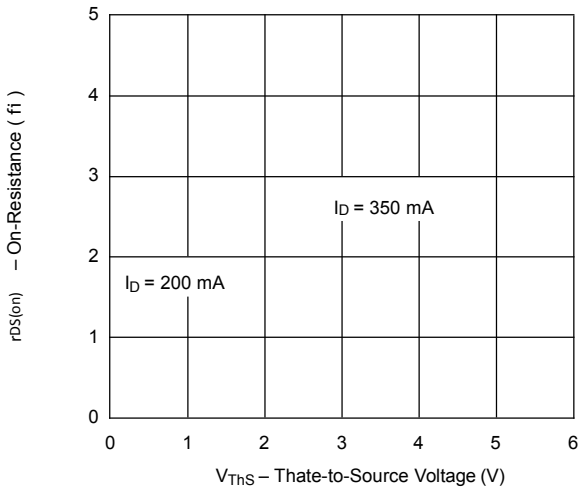


TYPICAh CHARACTERISTICS [T_A = 25°C UHhESS HOTED)

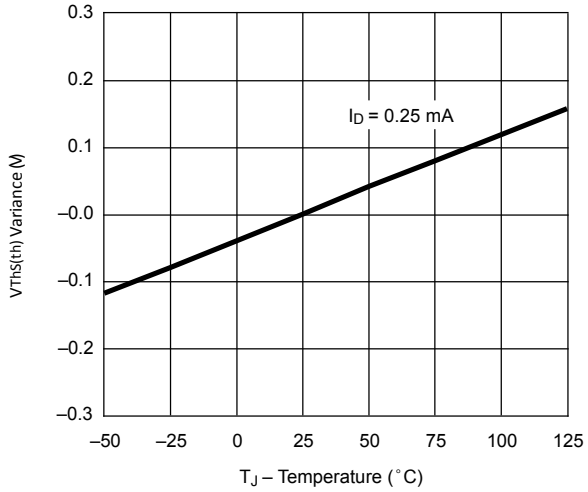
Source-Drain Diode Forward Voltage



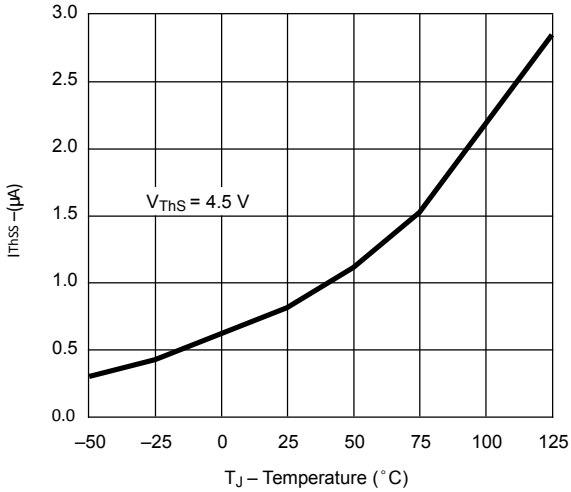
On-Resistance vs. Gate-to-Source Voltage



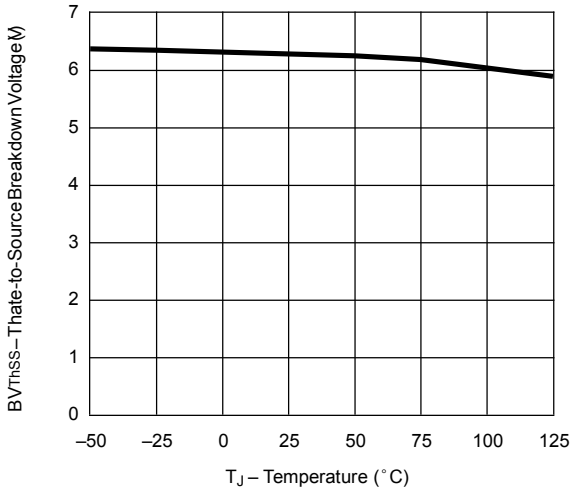
Threshold Voltage Variance vs. Temperature



I_{GSS} vs. Temperature

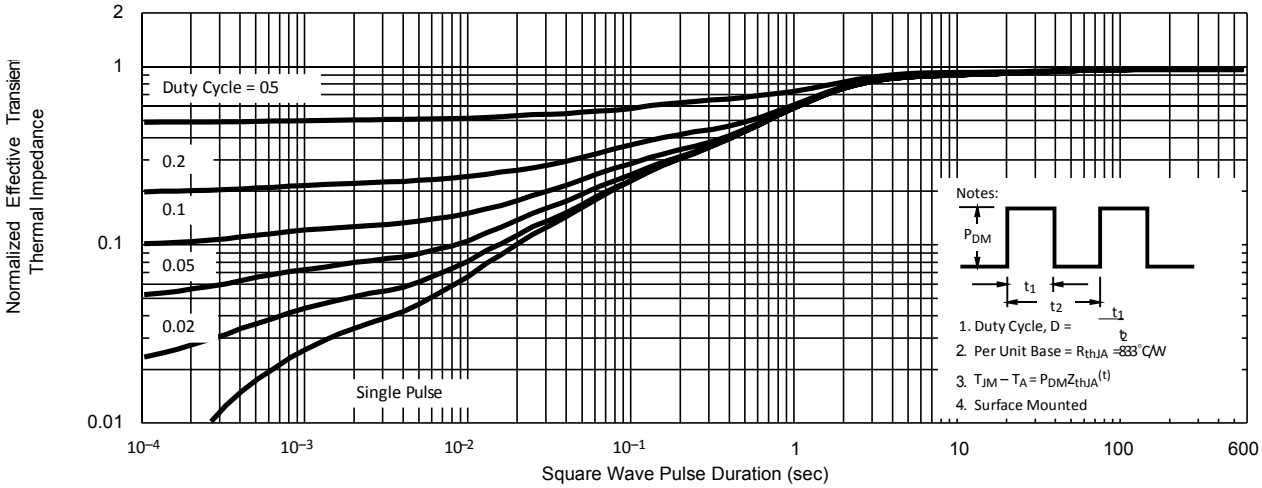


BV_{GSS} vs. Temperature

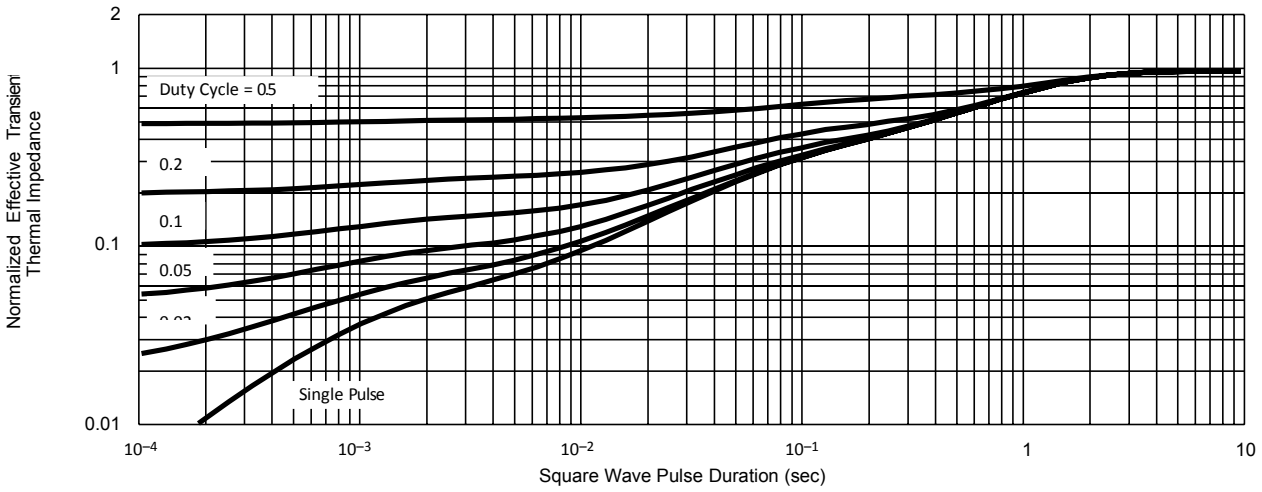


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)

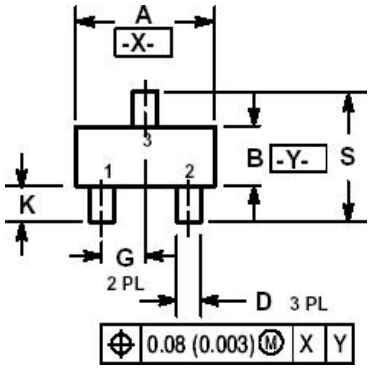
Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A)



Normalized Thermal Transient Impedance, Junction-to-Foot

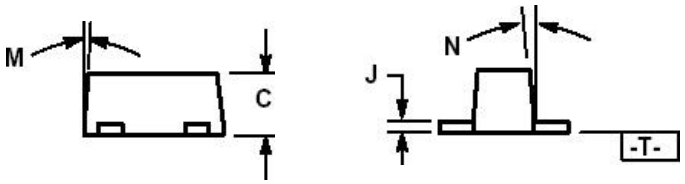


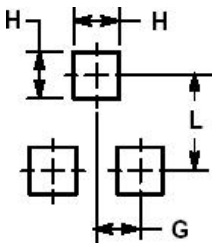
SC-89



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067





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